

FQA13N80_F109 Information



For Reference Only

Part Number FQA13N80_F109

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 12.6A TO-3P

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQA13N80_F109 Specifications

Manufacturer Part NumberFQA13N80_F109ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-3P-3, SC-65-3SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C12.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs88nC @ 10V	
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Gate Charge (Qg) (Max) @ Vgs 88nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds 3500pF @ 25V	
Vgs (Max) ±30V	
FET Feature -	
Power Dissipation (Max) 300W (Tc)	
Rds On (Max) @ Id, Vgs 750 mOhm @ 6.3A, 10V	
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	
Mounting Type Through Hole	
Supplier Device Package TO-3PN	
Package / Case TO-3P-3, SC-65-3	
Report 6	rrors?

FQA13N80_F109 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQA13N80_F109 Payment Methods



















FQA13N80_F109 Shipping Methods













If you have any question about FQA13N80_F109, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com